

SANYO	No.661E	2SK212
		N-Channel Junction Silicon FET

FM Tuner Applications

Features

- Ideal for FM tuners in low-voltage radios, car radios, etc.
- Small-sized package permitting 2SK212-applied sets to be made small and slim.
- Small Crss (Crss = 0.04pF typ).
- High $|Y_{fs}|$ ($|Y_{fs}| = 6.0\text{mS typ}$).

Absolute Maximum Ratings at Ta = 25°C

			unit
Gate-to-Drain Voltage	V _{GDO}	-20	V
Gate Current	I _G	10	mA
Drain Current	I _D	20	mA
Allowable Power Dissipation	P _D	200	mW
Junction Temperature	T _j	125	°C
Storage Temperature	T _{stg}	-55 to +125	°C

Electrical Characteristics at Ta = 25°C

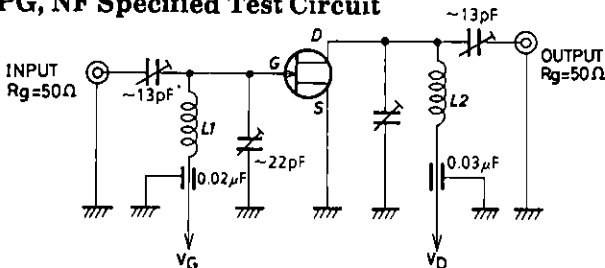
		min	typ	max	unit
G-D Breakdown Voltage	V _{(BR)GDO} I _G = -10μA	-20			V
Gate Cutoff Current	I _{GSS} V _{GS} = -0.5V, V _{DS} = 0			-10	nA
Drain Current	I _{DSS} V _{DS} = 5V, V _{GS} = 0	0.6*		12.0*	mA
Cutoff Voltage	V _{GS(off)} V _{DS} = 5V, I _D = 10μA			-2.5	V
Forward Transfer Admittance	$ Y_{fs} $ (1) V _{DS} = 5V, V _{GS} = 0, f = 1kHz	2.0	6.0		mS
	$ Y_{fs} $ (2) V _{DS} = 5V, V _{GS} = 0, f = 100MHz	2.0	6.0		mS
Input Capacitance	C _{iss} V _{DS} = 5V, V _{GS} = 0, f = 1MHz		4.0		pF
Reverse Transfer Capacitance	Crss V _{DS} = 5V, V _{GS} = 0, f = 1MHz		0.04	0.15	pF
Output Capacitance	C _{oss} V _{DS} = 5V, V _{GS} = 0, f = 1MHz		4.0		pF
Power Gain	PG V _{DS} = 5V, V _{GS} = 0, f = 100MHz		21		dB
Noise Figure	NF		3.5	6.0	dB

See specified Test Circuit.

* : The 2SK212 is classified by I_{DSS} as follows : (unit : mA)

0.6 C	1.5	1.2 D	3.0	2.5 E	6.0	5.0 F	12.0
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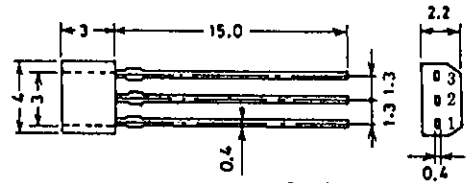
PG, NF Specified Test Circuit



L1: 1mmφ tin-plated wire, air core 10mmφ 4.5T
 L2: 1mmφ tin-plated wire, air core 10mmφ 3.5T

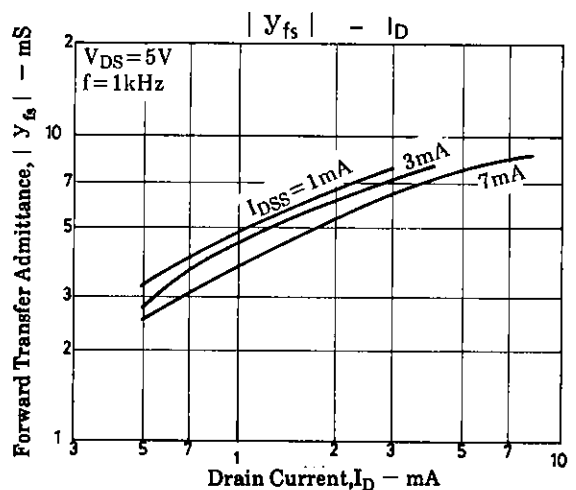
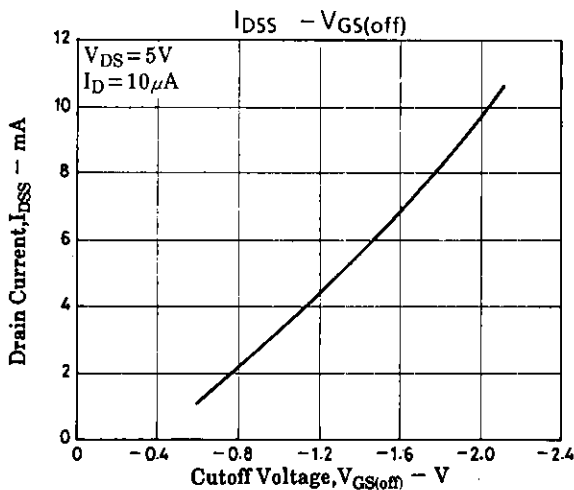
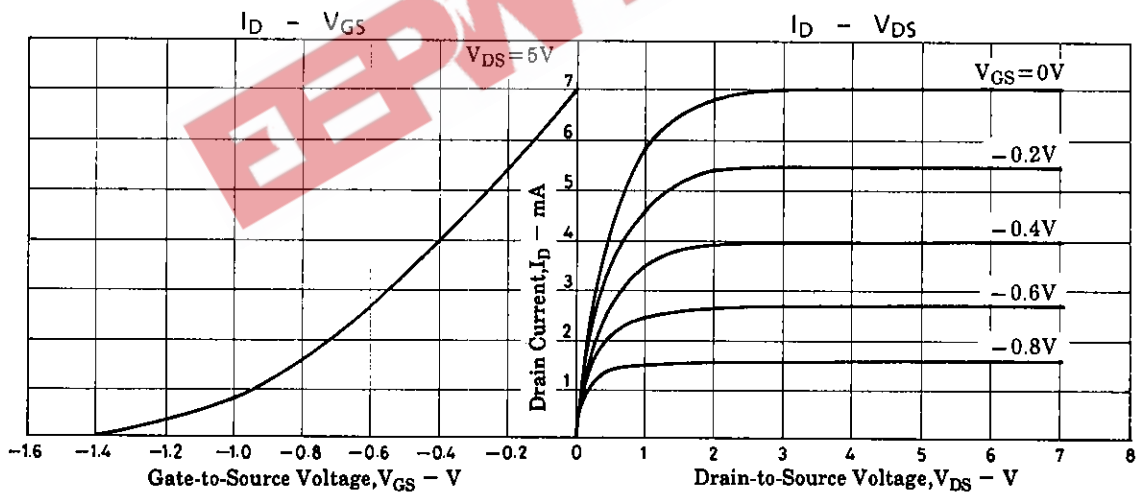
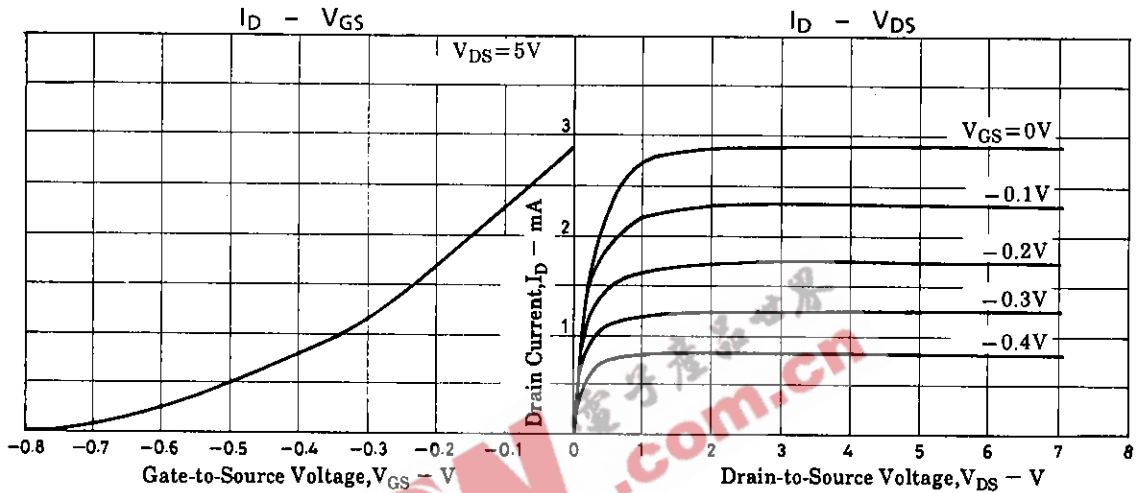
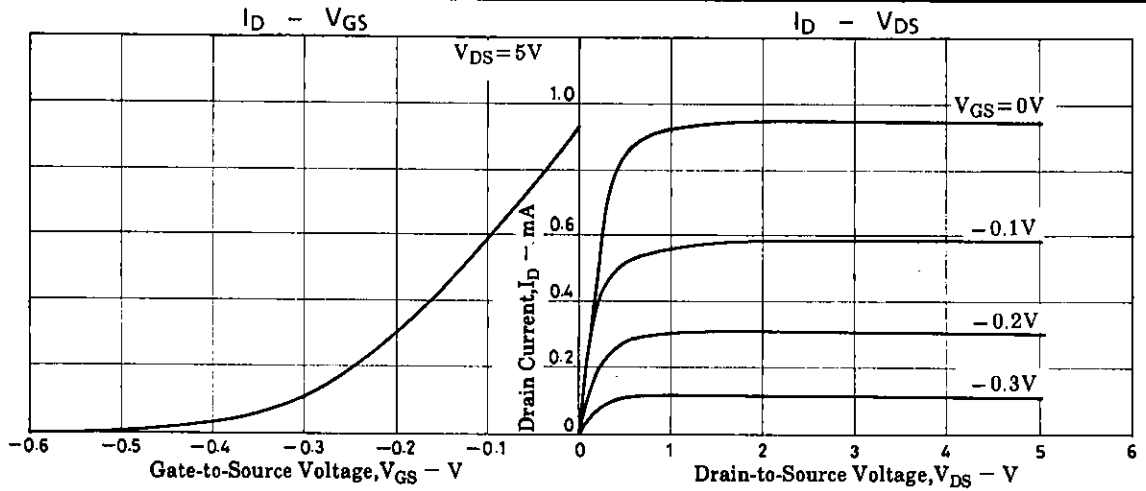
Package Dimensions 2040A

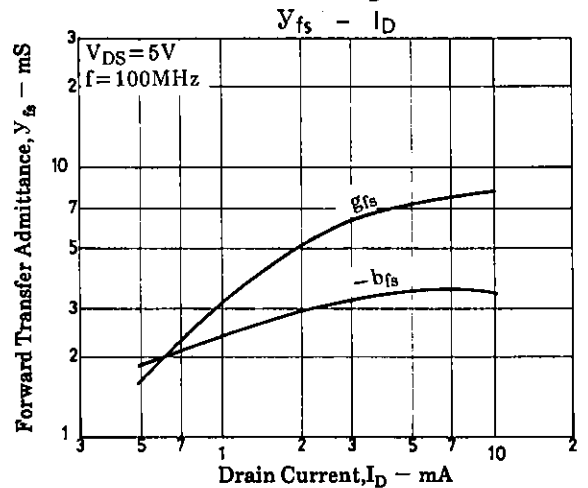
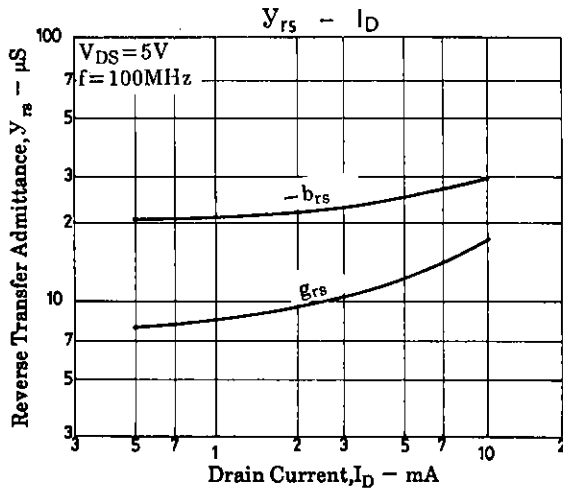
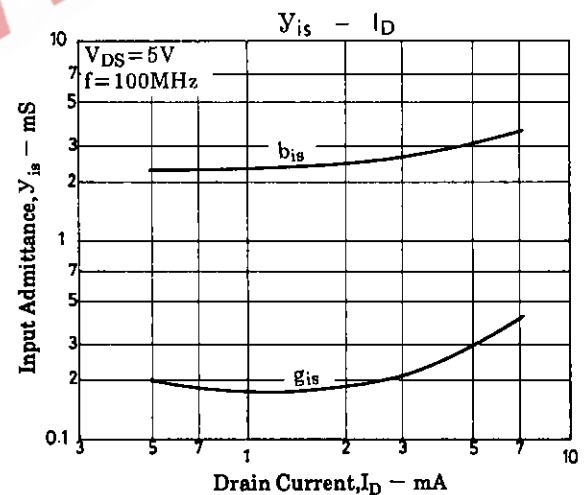
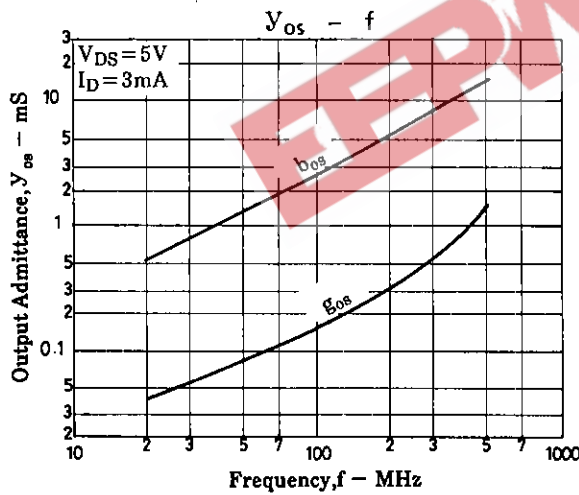
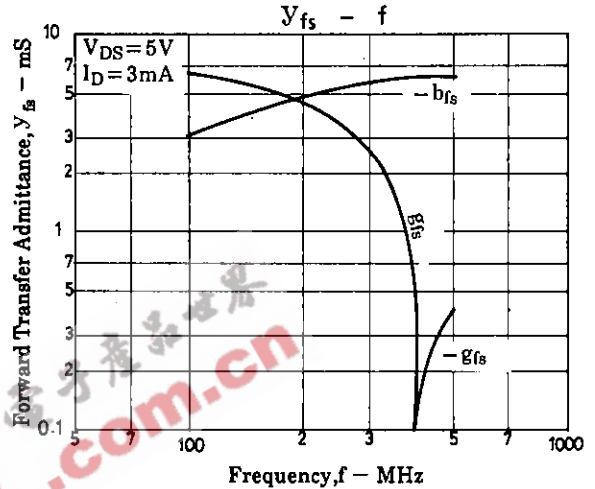
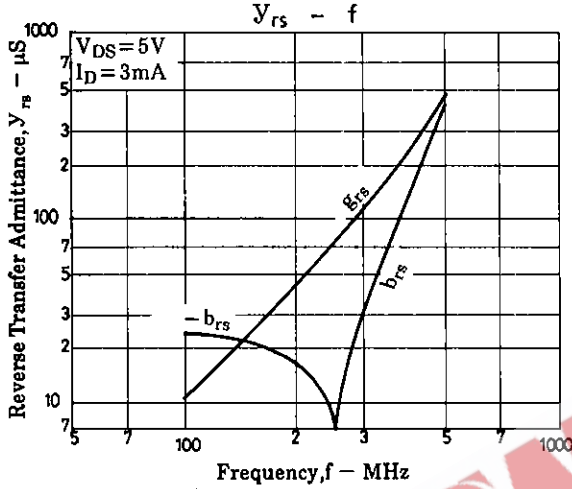
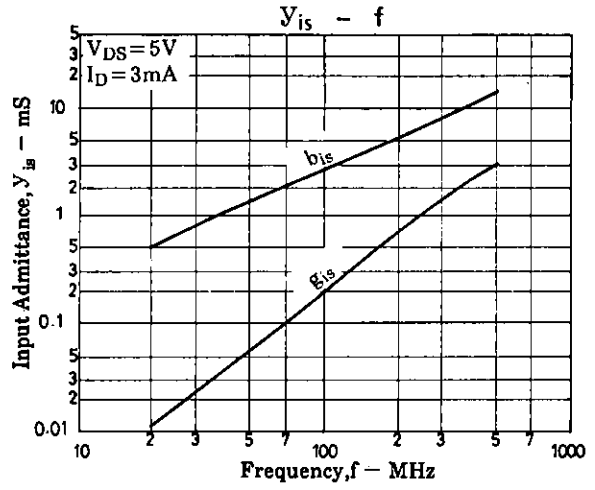
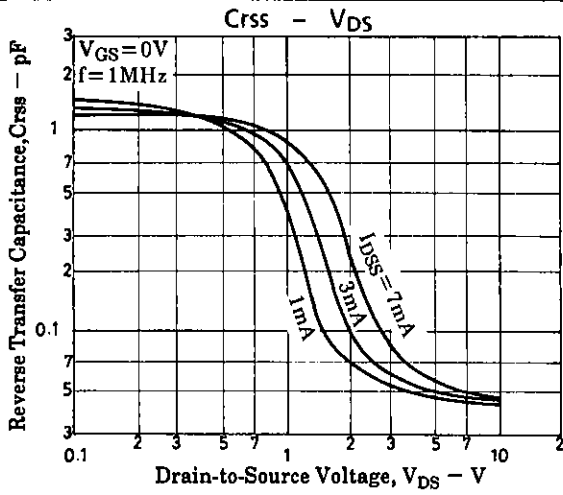
(unit : mm)

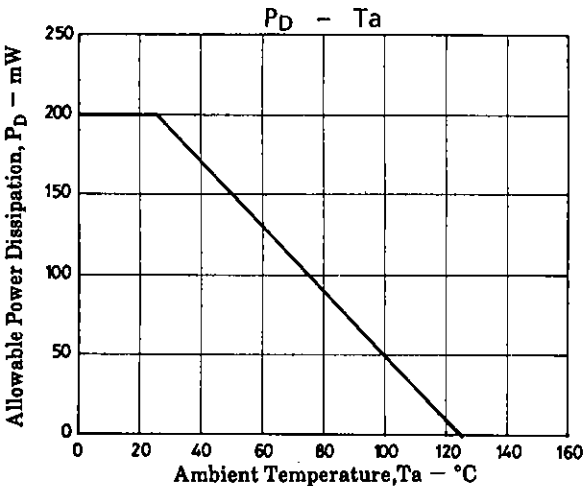
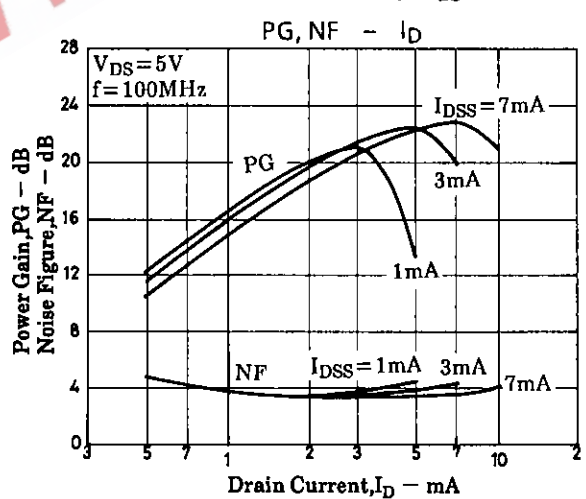
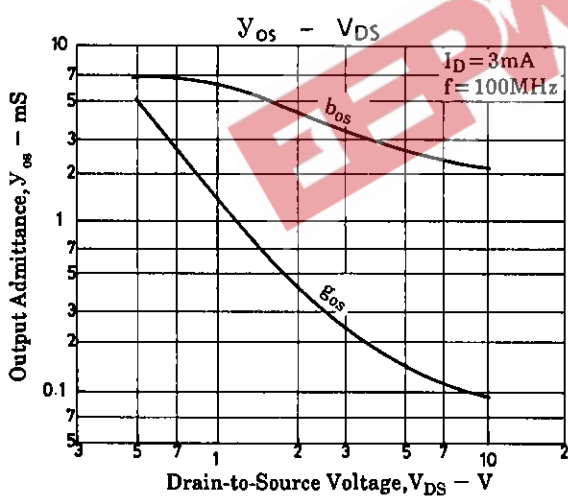
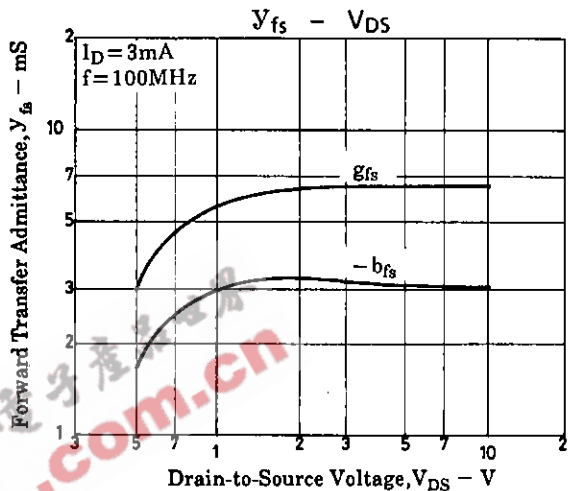
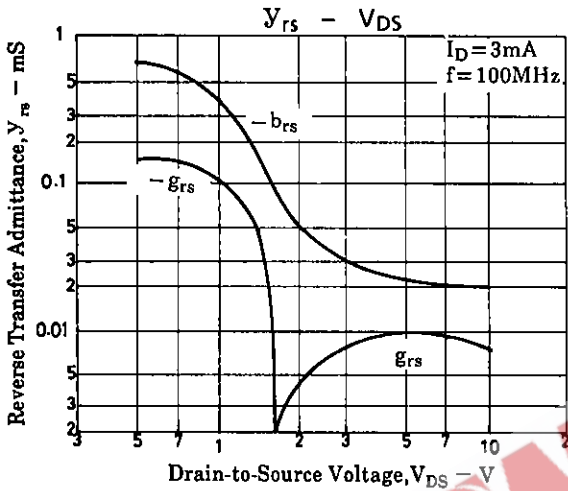
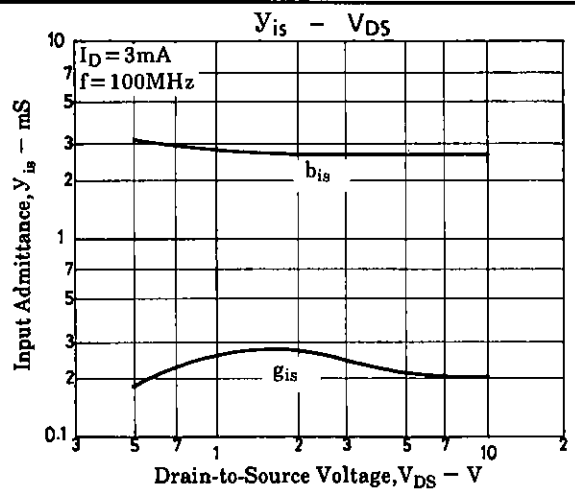
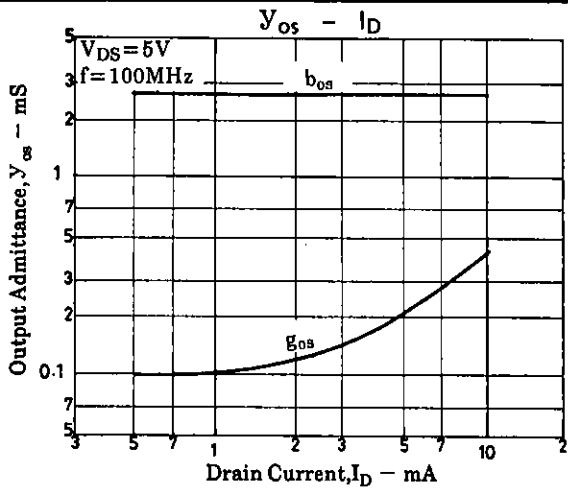


1: Drain
 2: Source
 3: Gate

SANYO: SPA







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